CMOS-Compatible SOI MESFETS for Radiation-Hardened DC-to-DC Converters

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A radiation-tolerant transistor switch has been developed that can operate between −196 and +150 °C for DC-to-DC power conversion applications. A prototype buck regulator component was demonstrated to be performing well after a total ionizing dose of 300 krad(Si). The prototype buck converters showed good efficiencies at ultra-high switching speeds in the range of 1 to 10 MHz. Such high switching frequency will enable smaller, lighter buck converters to be developed as part of the next project. Switching regulators are widely used in commercial applications including portable consumer electronics.

Silicon Heat Pipe Array

Applications include high-power electronic circuits or components such as microprocessors, diode lasers, and concentrated solar collectors.

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Improved methods of heat dissipation are required for modern, high-power-density electronic systems. As increased functionality is progressively compacted into decreasing volumes, this need will be exacerbated. High-performance chip power is predicted to increase monotonically and rapidly with time. Systems utilizing these chips are currently reliant upon decades of old cooling technology.

Heat pipes offer a solution to this problem. Heat pipes are passive, self-contained, two-phase heat dissipation devices. Heat conducted into the device through a wick structure converts the working fluid into a vapor, which then releases the heat via condensation after being transported away from the heat source. Heat pipes have high thermal conductivities, are inexpensive, and have been utilized in previous space missions. However, the cylindrical geometry of commercial heat pipes is a poor fit to the planar geometries of microelectronic assemblies, the copper that commercial heat pipes are typically constructed of is a poor CTE (coefficient of thermal expansion) match to the types of high-power die that would potentially be attached or integrated to the heat-generating elements to the heat pipe. Fabrication of the heat pipe and the wick structure are co-fabricated. This enables stress-free operation of the device over temperature, as the device is of homogenous material construction. Adhesion of the wick to the structure is not an issue, as the wick is etched from the structure itself, and is not grown or deposited.

(1) Co-fabrication of the heat pipe structure and the wick. A black Si wick structure is utilized so that the housing of the heat pipe and the wick structure can be co-fabricated. This enables stress-free operation of the device over temperature, as the device is of homogenous material construction. Adhesion of the wick to the structure is not an issue, as the wick is etched from the structure itself, and is not grown or deposited.

(2) Direct attachment or integration of heat-generating elements to the heat pipe. Fabrication of the heat pipe from Si allows stress-free, expansion-matched attachment of high-power semiconductor components or even the direct integration of such components. For example, high-power...